



DSS4160T

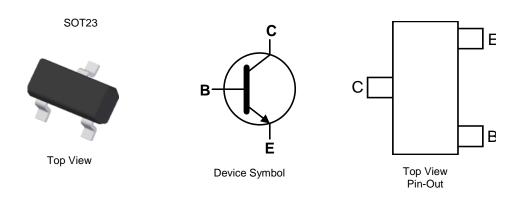
60V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

- BV_{CEO} > 60V
- I_C = 1A High Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- R_{CE(sat)} = 280mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(sat)} < 280mV @ 1A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated leads, Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4160T-7	AEC-Q101	ZN9	7	8	3,000
DSS4160TQ-7	Automotive	ZN9	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

ZN9

SOT23

ZN9 = Product Type Marking Code



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Collector Current	I _{CM}	2	Α
Base Current	IΒ	300	mA
Peak Base Current	I _{BM}	1	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	725	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	172	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	79	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

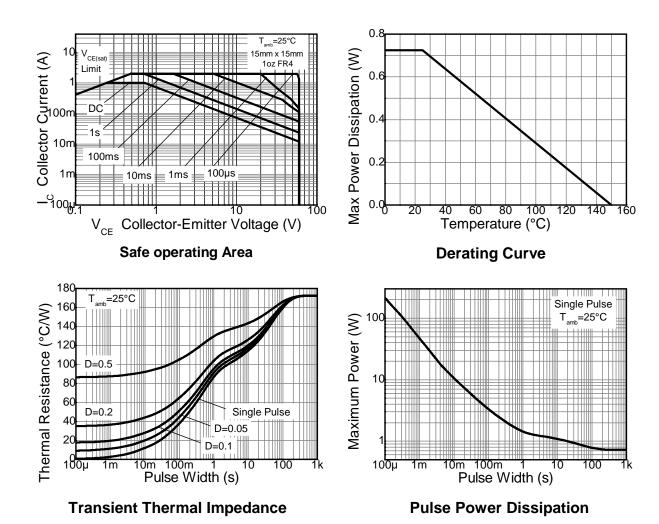
^{6.} For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{7.} Thermal resistance from junction to solder-point (at the end of collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



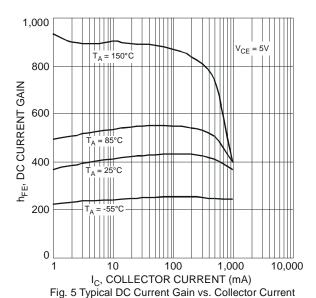


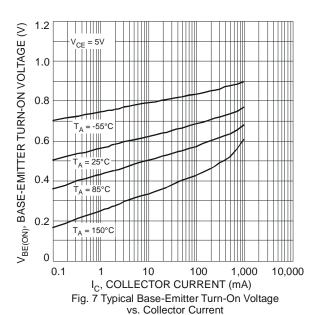
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

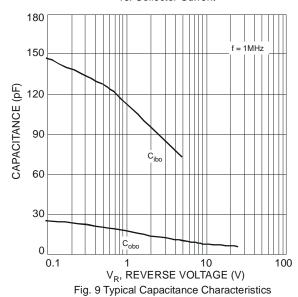
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
Collector-Base Breakdown Voltage	BV _{CBO}	80	_	_	V	$I_C = 100\mu A$	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	_	_	V	$I_C = 10mA$	
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	V	I _E = 100μA	
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 60V, I _E = 0	
Collector-Base Cuton Current			_	50	μA	$V_{CB} = 60V$, $I_E = 0$, $T_A = +150$ °C	
Collector Cutoff Current	I _{CES}		_	100	nA	$V_{EB} = 60V, I_{BE} = 0$	
Emitter-Base Cutoff Current	I _{EBO}		_	100	nA	$V_{EB} = 5V, I_C = 0$	
		250	_	_		V _{CE} = 5V, I _C = 1mA	
DC Current Gain (Note 9)	h _{FE}	200	_	_	_	V _{CE} = 5V, I _C = 500mA	
		100	_	_		V _{CE} = 5V, I _C = 1A	
	V _{CE(sat)}		_	115	mV	I _C = 100mA, I _B = 1mA	
Collector-Emitter Saturation Voltage (Note 9)				150		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$	
				280		$I_C = 1A, I_B = 100mA$	
Equivalent On-Resistance	R _{CE(sat)}			280	mΩ	I _E = 1A, I _B = 100mA	
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.1	V	$I_C = 1A, I_B = 50mA$	
Base-Emitter Turn-on Voltage	V _{BE(on)}			0.9	V	$V_{CE} = 5V$, $I_C = 1A$	
Transition Frequency	f _T	150			MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz	
Output Capacitance	C_{obo}		_	10	pF	V _{CB} = 10V, f = 1MHz	
Turn-On Time	ton		63	_	ns		
Delay Time	t _d		33	_	ns		
Rise Time	t _r		30		ns	$V_{CC} = 10V, I_C = 0.5A,$ $I_{B1} = -I_{B2} = 25mA$	
Turn-Off Time	t _{off}		420		ns		
Storage Time	ts		380		ns		
Fall Time	t _f	_	40	_	ns		

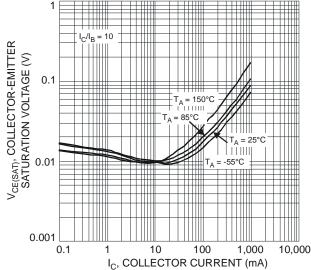
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



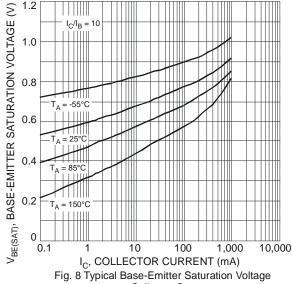








I_C, COLLECTOR CURRENT (mA)
Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current



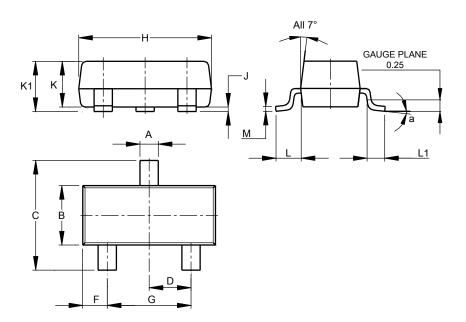
vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

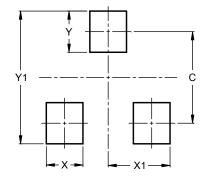


SOT23				
Dim	Min	Max	Тур	
Α	0.37	0.51	0.40	
В	1.20	1.40	1.30	
C	2.30	2.50	2.40	
D	0.89	1.03	0.915	
F	0.45	0.60	0.535	
G	1.78	2.05	1.83	
Н	2.80	3.00	2.90	
7	0.013	0.10	0.05	
K	0.890	1.00	0.975	
K1	0.903	1.10	1.025	
١	0.45	0.61	0.55	
L1	0.25	0.55	0.40	
M	0.085	0.150	0.110	
а	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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